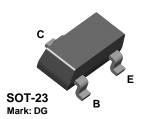


BCW68G



PNP General Purpose Amplifier

This device is designed for general purpose amplifier and switching applications at currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	45	V
V _{CBO}	Collector-Base Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		*BCW68G		
P _D	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

(continued)

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 		Olla	acie	1131163

TA = 25°C unless otherwise noted

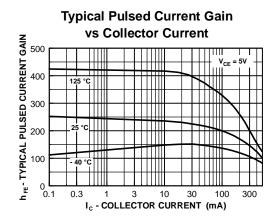
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAF	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	45		V
V _{(BR)CES}	Collector-Base Breakdown Voltage	I _C = 10 μA	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
I _{CES}	Collector-Cutoff Current	V _{CE} = 45 V V _{CE} = 45 V, T _A = 150 °C		20 10	nA μA
I _{EBO}	Emitter-Cutoff Current	V _{EB} = 4.0 V		20	nA
h _{FE}	ACTERISTICS DC Current Gain Collector-Emitter Saturation Voltage	I _C = 10 mA, V _{CE} = 1.0 V I _C = 100 mA, V _{CE} = 1.0 V I _C = 300 mA, V _{CE} = 1.0 V I _C = 300 mA, I _B = 30 mA	120 160 60	400	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		2.0	V
SMALL SI	GNAL CHARACTERISTICS Current Gain - Bandwidth Product	I _C = 20 mA, V _{CE} = 10 V, f = 100 MHz	100		MHz
C _{obo}	Ouput Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		18	pF
C _{ibo}	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		105	pF
NF	Noise Figure	$I_{C} = 0.2 \text{ mA V}, V_{CE} = 5.0 \text{ V}, \\ R_{S} = 1.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz}, \\ B_{W} = 200 \text{ Hz}$		10	dB

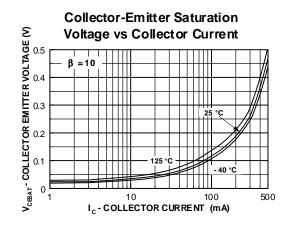
NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

Spice Model

 $PNP \ (Is=650.6E-18 \ Xti=3 \ Eg=1.11 \ Vaf=115.7 \ Bf=231.7 \ Ne=1.829 \ Is=54.81f \ Ikf=1.079 \ Xtb=1.5 \ Br=3.563 \ Nc=2 \ Isc=0 \ Ikr=0 \ Rc=.715 \ Cjc=14.76p \ Mjc=.5383 \ Vjc=.75 \ Fc=.5 \ Cje=19.82p \ Mje=.3357 \ Vje=.75 \ Tr=111.3n \ Tf=603.7p \ Itf=.65 \ Vtf=5 \ Xtf=1.7 \ Rb=10)$

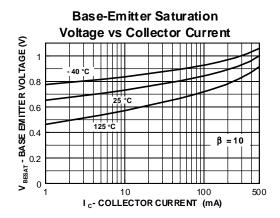
Typical Characteristics

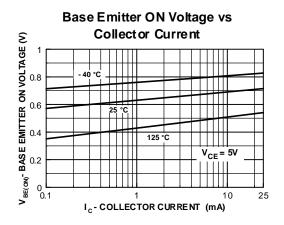


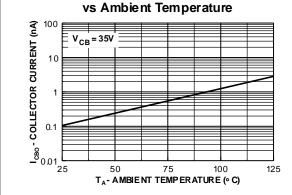


(continued)

Typical Characteristics (continued)



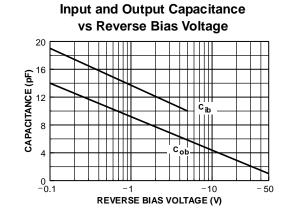


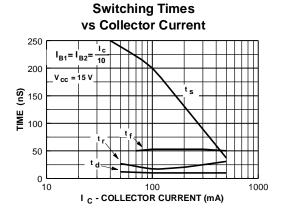


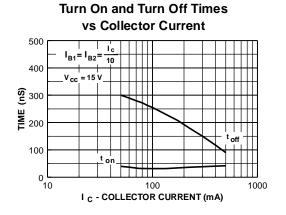
TA- AMBIENT TEMPERATURE (° C)

125

Collector-Cutoff Current

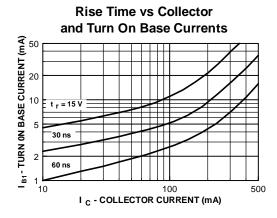


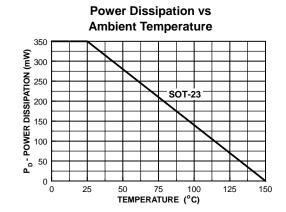




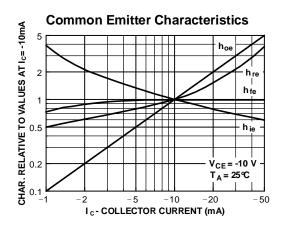
(continued)

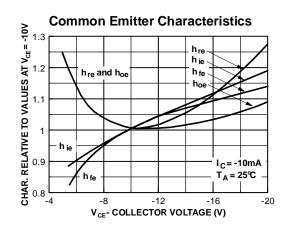
Typical Characteristics (continued)

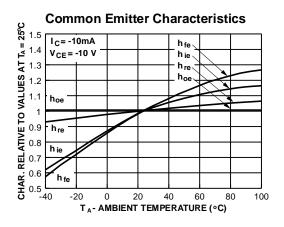




Typical Common Emitter Characteristics (f = 1.0kHz)







(continued)

Test Circuits

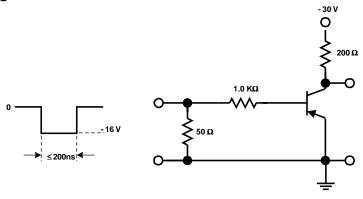


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

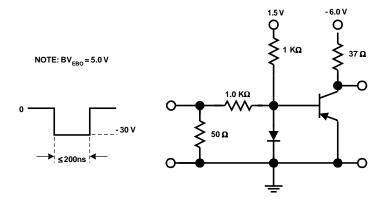
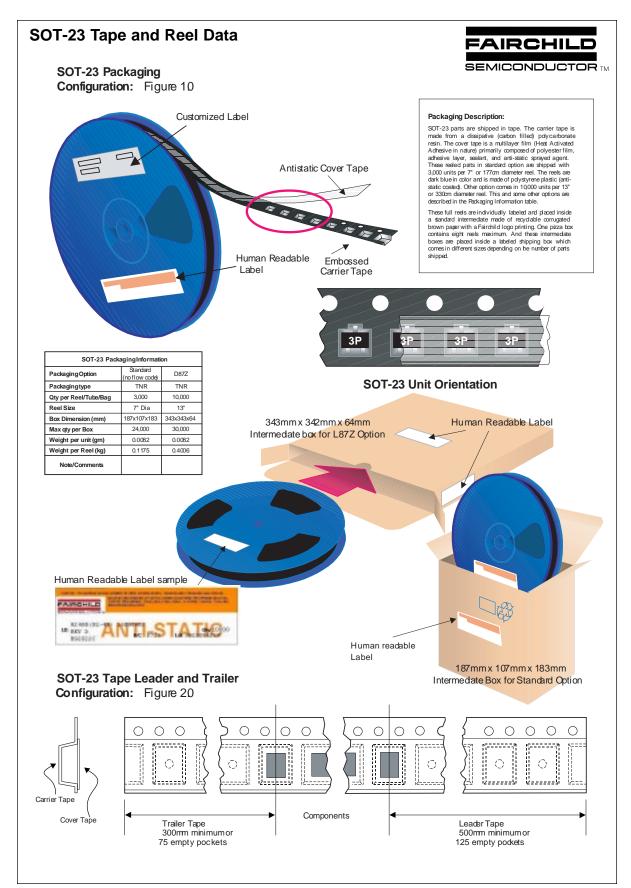


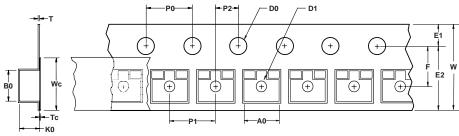
FIGURE 2: Saturated Turn-Off Switching Time Test Circuit



SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



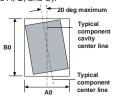
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

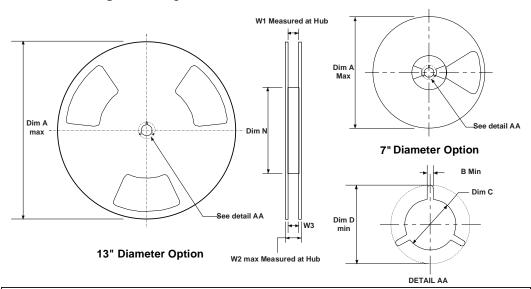


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

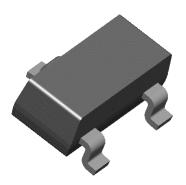
SOT-23 Reel Configuration: Figure 4.0

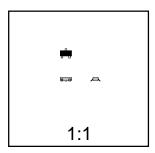


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



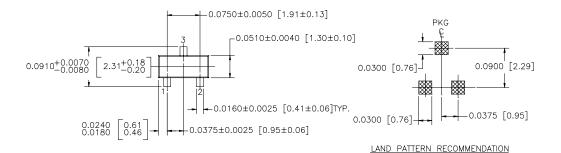
SOT-23 (FS PKG Code 49)

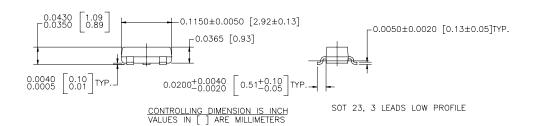




Scale 1:1 on letter size paper Dimensions shown below are in:

inches [millimeters]
Part Weight per unit (gram): 0.0082





NOTE : UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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